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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of: RINERSON et al.

Attorney Docket No.: UNTYP027

Application No.: 10/665,882

Examiner: not yet assigned

Filed: September 19, 2003

Group: 2811

Title: RESISTIVE MEMORY DEVICE WITH A  
TREATED INTERFACE

Confirmation No.: 6771

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450 on JUNE 25, 2004.

Signed: \_\_\_\_\_

Sally Zumba

**INFORMATION DISCLOSURE STATEMENT  
37 CFR §§1.56 AND 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir/Ms.:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. UNTYP027).

Respectfully submitted,

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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	<b>UNTYP027</b> Applicant: <b>RINERSON et al.</b> Filing Date <b>September 19, 2003</b>	<b>10/665,882</b>  Group <b>2811</b>

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,204,139	3/2001	Liu et al.			

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1							

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	Baikalov et al., "Field-Driven Hysteric and Reversible Resistive Switch at the Ag Pro <sub>0.7</sub> Ca <sub>0.3</sub> MnO <sub>3</sub> Interface", May 2003, Department of Physics and Texas Center for Superconductivity, University of Houston, pp. 1-8.
	C2	Beck et al., "Reproducible switching effect in thin oxide films for memory applications", July 2000, Applied Physics Letters, Vol. 77, No. 1, pp. 139-141.
	C3	Gerstner et al., "Nonvolatile memory effects in nitrogen doped tetrahedral amorphous carbon thin films," November 1998, Journal of Applied Physics, Vol. 84, No. 10, pp. 5647-5651.
	C4	Mieville et al., "Transport across conducting ferromagnetic oxide/metal interfaces", September 1998, Applied Physics Letters, Vol. 73, No. 12, pp. 1736-1738.
	C5	Liu et al., "A New Concept for Non-Volatile Memory: The Electric-Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films", University of Houston, pp. 1-7.
	C6	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", May 2000, Applied Physics Letters, Vol. 76, No. 19, pp. 2749-2751.
	C7	Plecken et al., "Degradation of LaMnO <sub>3-y</sub> surface layer in LaMnO <sub>3-y</sub> /metal interface", July 2002, Applied Physics Letters, Vol. 81, No. 5, pp. 859-861.
	C8	Rossel et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", September 2001, Journal of Applied Physics, Vol. 90, No. 6, pp. 2892-2898.

	C9	Simmons et al., "New conduction and reversible memory phenomena in thin insulating films", 1967, Proc. Roy. Soc. A., Vol. 301, pp. 77-102.
	C10	Tulina et al., "Reproducible switching in normal metal-manganite single crystal point contacts with memory effect", 2003, Physica C., Vol. 385, pp. 563-567.
	C11	Tulina et al., "Reversible electrical switching at the $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+y}$ surface in the normal metal – $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+y}$ single crystal heterojunction," 2001, Physica C., Vol. 366, pp. 23-30.
	C12	Watanabe et al., "Current-driver insulator-conductor transition and nonvolatile memory in chromium-doped $\text{SrTiO}_3$ single crystals," June 2001, Applied Physics Letters, Vol. 78, No. 23, pp. 3738-3740.
	C13	Ziese et al., "Voltage-controlled colossal magnetoresistance in manganite/normal-metal heterostructures", February 1998, Physical Review B, Vol. 57, No. 5, pp. 2963-2966.
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.